



# BTA208X-1000C0

3Q Hi-Com Triac

22 May 2014

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This triac is intended for use in motor control circuits where very high blocking voltage, high static and dynamic  $dV/dt$  as well as high  $dI_{com}/dt$  can occur. This "series C0" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- Isolated mounting base package
- Optimized for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high voltage capability

## 3. Applications

- Compressor starting control circuits
- General purpose motor controls
- Reversing induction motor controls e.g. vertical axis washing machines

## 4. Quick reference data

Table 1. Quick reference data

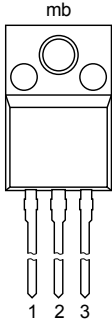
| Symbol                        | Parameter                            | Conditions                                                                                                            | Min | Typ | Max  | Unit |
|-------------------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |                                                                                                                       | -   | -   | 1000 | V    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 65   | A    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_h \leq 73\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>    | -   | -   | 8    | A    |
| <b>Static characteristics</b> |                                      |                                                                                                                       |     |     |      |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_2+ G+$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                | 5   | 11  | 35   | mA   |



| Symbol | Parameter | Conditions                                                                                        | Min | Typ | Max | Unit |
|--------|-----------|---------------------------------------------------------------------------------------------------|-----|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7 | 5   | 14  | 35  | mA   |
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7 | 5   | 25  | 35  | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description             | Simplified outline                                                                                          | Graphic symbol                                                                                    |
|-----|--------|-------------------------|-------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|
| 1   | T1     | main terminal 1         |  <p>TO-220F (SOT186A)</p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2         |                                                                                                             |                                                                                                   |
| 3   | G      | gate                    |                                                                                                             |                                                                                                   |
| mb  | n.c.   | mounting base; isolated |                                                                                                             |                                                                                                   |

## 6. Ordering information

Table 3. Ordering information

| Type number        | Package |                                                                                                     |         |
|--------------------|---------|-----------------------------------------------------------------------------------------------------|---------|
|                    | Name    | Description                                                                                         | Version |
| BTA208X-1000C0     | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |
| BTA208X-1000C0/L01 | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

## 7. Marking

Table 4. Marking codes

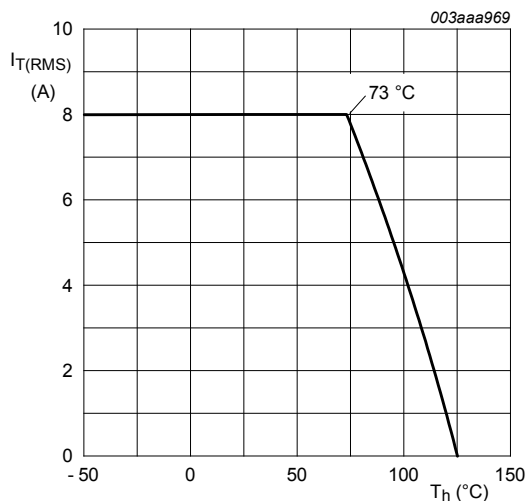
| Type number        | Marking code      |
|--------------------|-------------------|
| BTA208X-1000C0     |                   |
| BTA208X-1000C0/L01 | BTA208X-1000C0L01 |

## 8. Limiting values

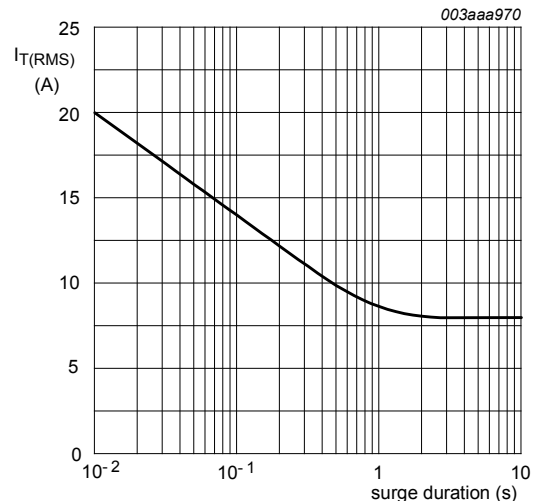
**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol              | Parameter                            | Conditions                                                                                                                       | Min | Max  | Unit                   |
|---------------------|--------------------------------------|----------------------------------------------------------------------------------------------------------------------------------|-----|------|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |                                                                                                                                  | -   | 1000 | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_h \leq 73^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>           | -   | 8    | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 65   | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$                                                 | -   | 71   | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN                                                                                                       | -   | 21   | $\text{A}^2\text{s}$   |
| $di_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 12\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$                     | -   | 100  | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |                                                                                                                                  | -   | 2    | A                      |
| $P_{\text{GM}}$     | peak gate power                      |                                                                                                                                  | -   | 5    | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period                                                                                                            | -   | 0.5  | W                      |
| $T_{\text{stg}}$    | storage temperature                  |                                                                                                                                  | -40 | 150  | $^\circ\text{C}$       |
| $T_{\text{j}}$      | junction temperature                 |                                                                                                                                  | -   | 125  | $^\circ\text{C}$       |



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_h = 73^\circ\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

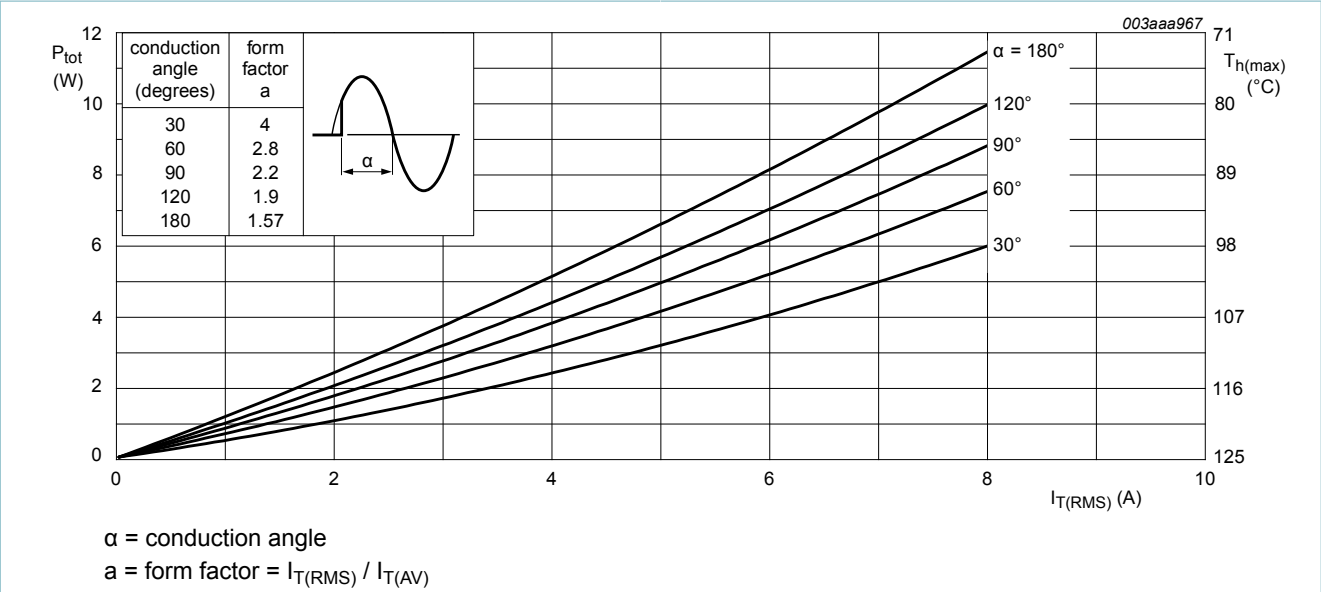


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

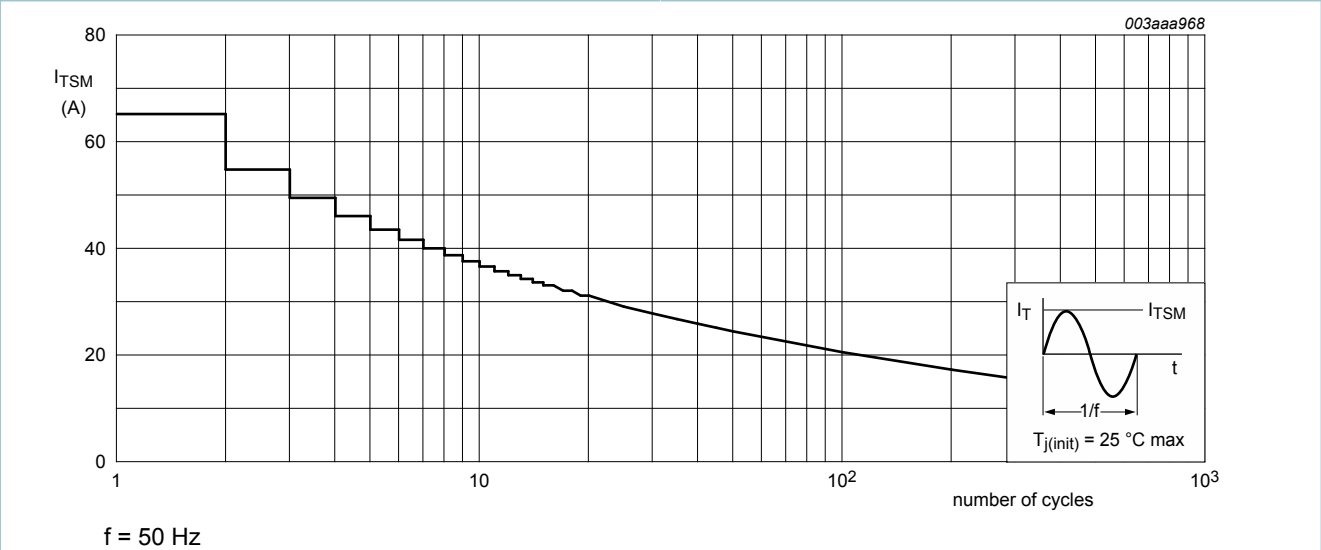
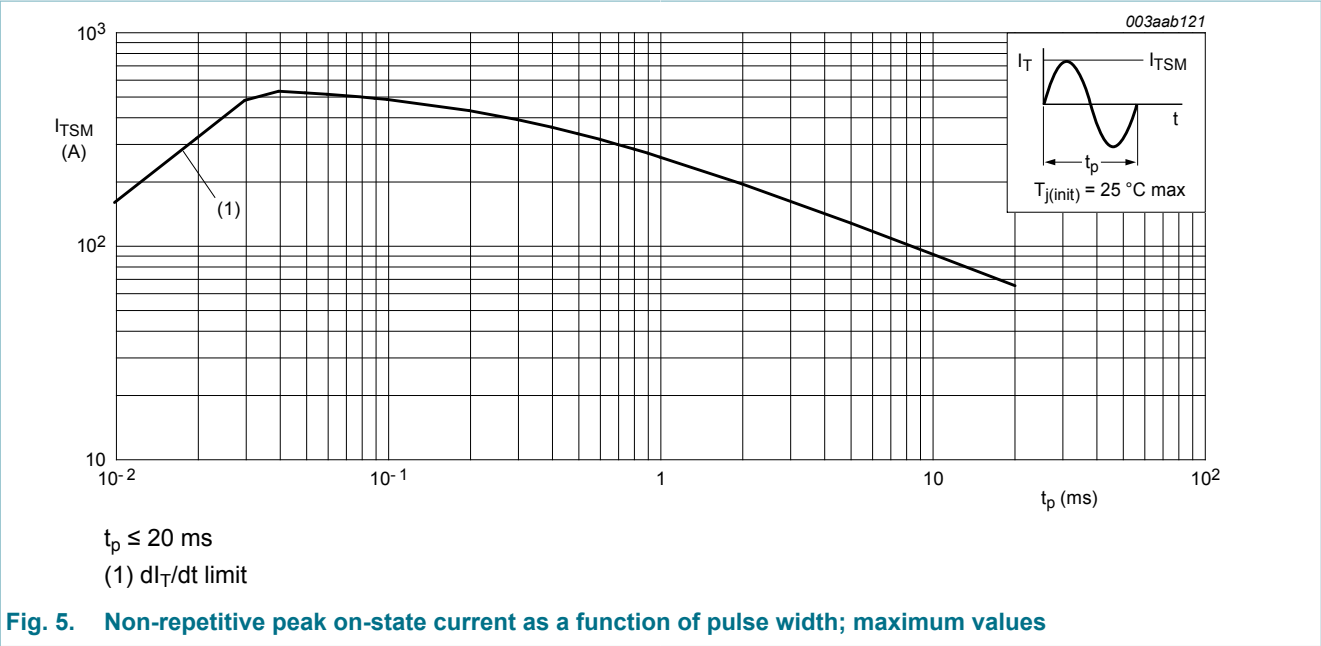


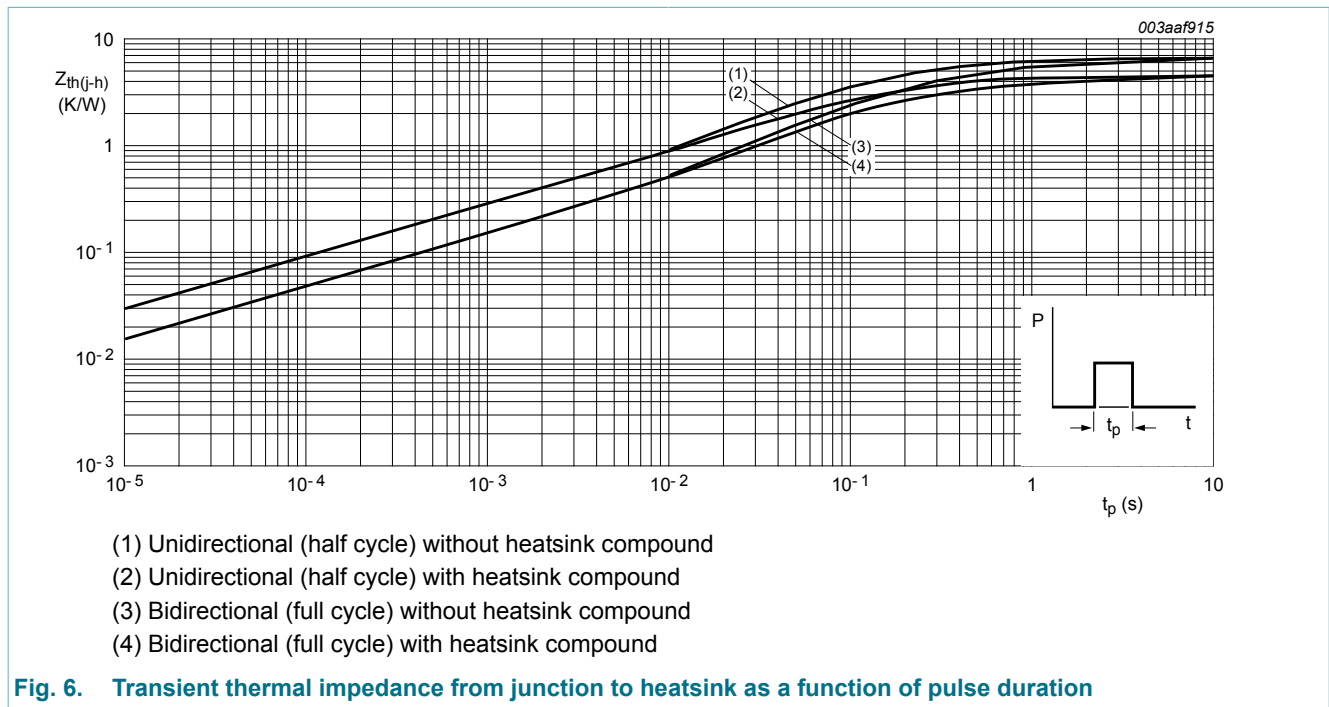
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol        | Parameter                                    | Conditions                                                  | Min | Typ | Max | Unit |
|---------------|----------------------------------------------|-------------------------------------------------------------|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | full cycle or half cycle; with heatsink compound; Fig. 6    | -   | -   | 4.5 | K/W  |
|               |                                              | full cycle or half cycle; without heatsink compound; Fig. 6 | -   | -   | 6.5 | K/W  |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient  | in free air                                                 | -   | 55  | -   | K/W  |



## 10. Isolation characteristics

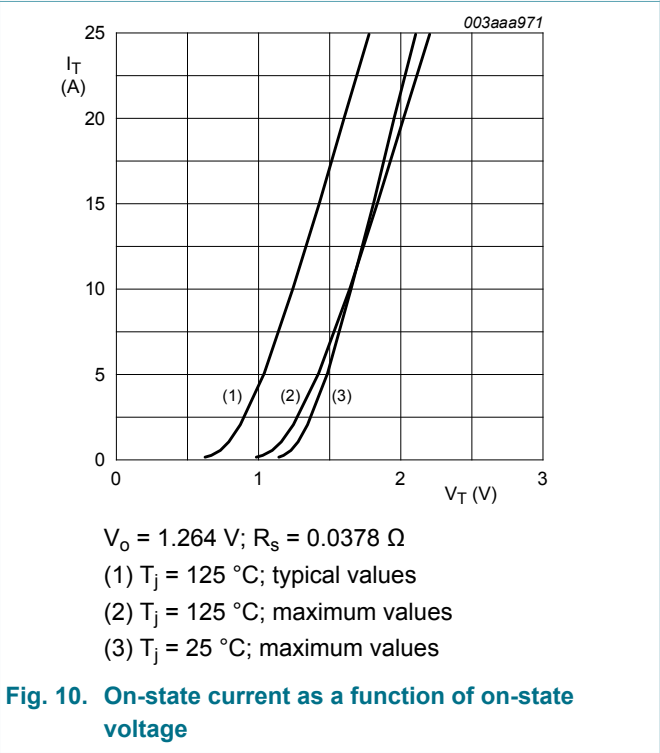
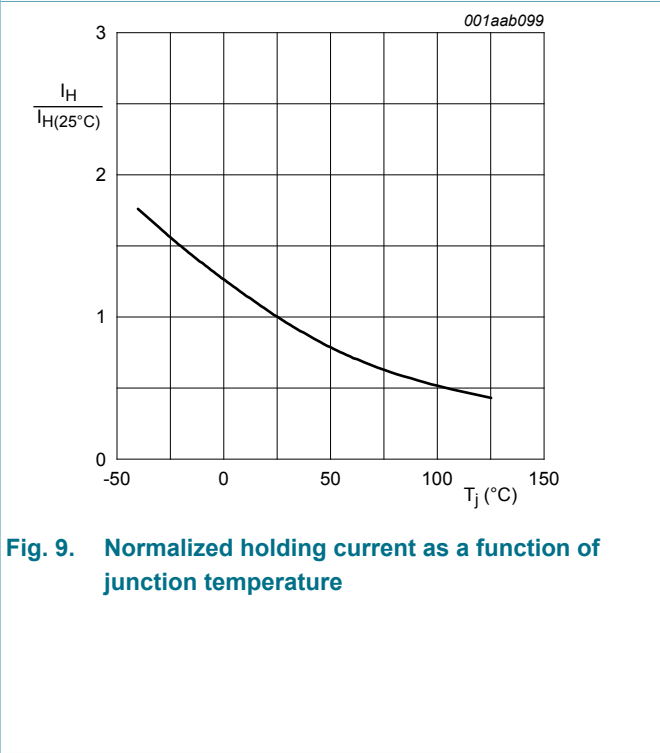
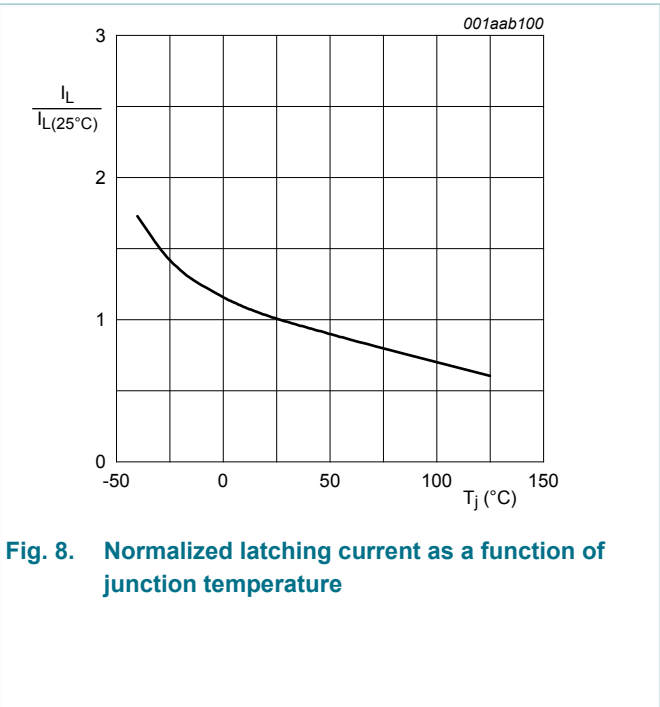
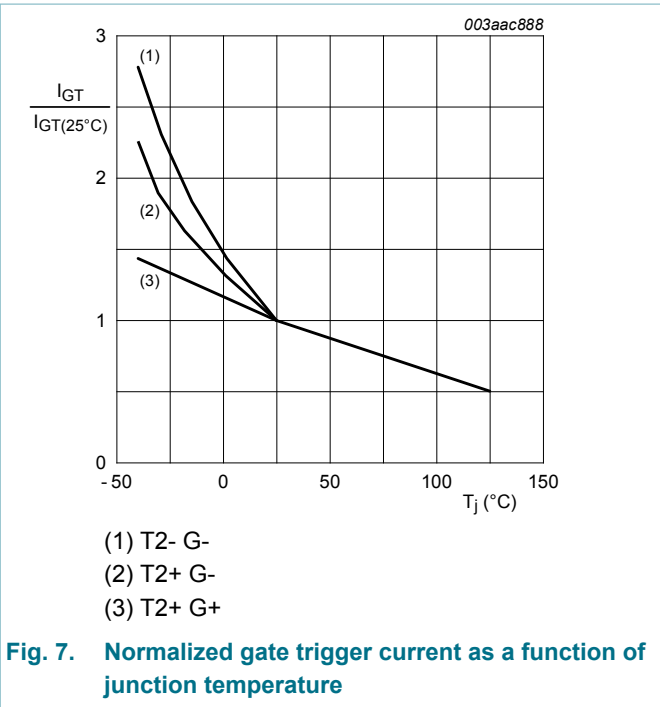
Table 7. Isolation characteristics

| Symbol          | Parameter             | Conditions                                                                                                                                                                     | Min | Typ | Max  | Unit |
|-----------------|-----------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$ | -   | -   | 2500 | V    |
| $C_{isol}$      | isolation capacitance | from main terminal 2 to external heatsink; $f = 1\text{ MHz}$ ; $T_h = 25\text{ }^\circ\text{C}$                                                                               | -   | 10  | -    | pF   |

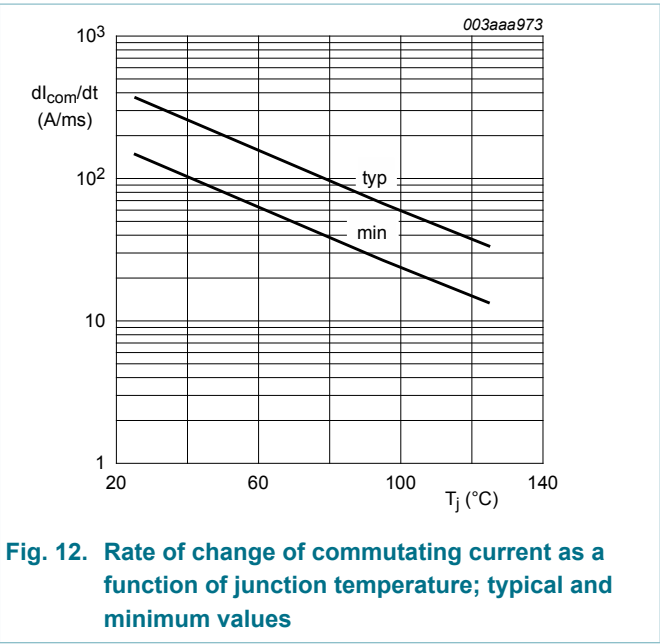
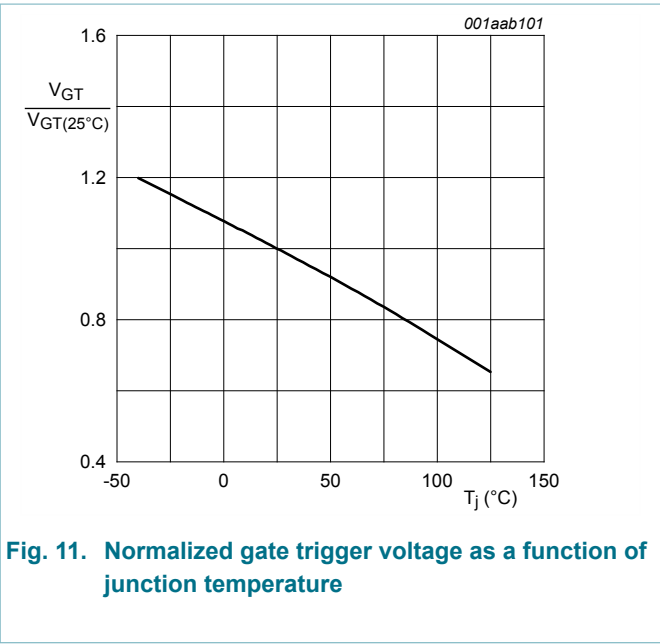
## 11. Characteristics

Table 8. Characteristics

| Symbol                         | Parameter                             | Conditions                                                                                                                                                                                           | Min  | Typ  | Max  | Unit             |
|--------------------------------|---------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|------------------|
| <b>Static characteristics</b>  |                                       |                                                                                                                                                                                                      |      |      |      |                  |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                                                                    | 5    | 11   | 35   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                                                                    | 5    | 14   | 35   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                                                                    | 5    | 25   | 35   | mA               |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                                                                    | -    | 25   | 50   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                                                                    | -    | 48   | 75   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                                                                    | -    | 30   | 50   | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>                                                                                                                      | -    | 20   | 50   | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 10\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                                                                                     | -    | 1.3  | 1.65 | V                |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                                                                                           | -    | 0.7  | 1    | V                |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                                                      | 0.25 | 0.4  | -    | V                |
| $I_D$                          | off-state current                     | $V_D = 1000\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                                                                            | -    | 0.1  | 0.5  | mA               |
| <b>Dynamic characteristics</b> |                                       |                                                                                                                                                                                                      |      |      |      |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 670\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit                                                              | 1500 | 4000 | -    | V/ $\mu\text{s}$ |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 8\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 12</a> | 12   | 32   | -    | A/ms             |







12. Package outline

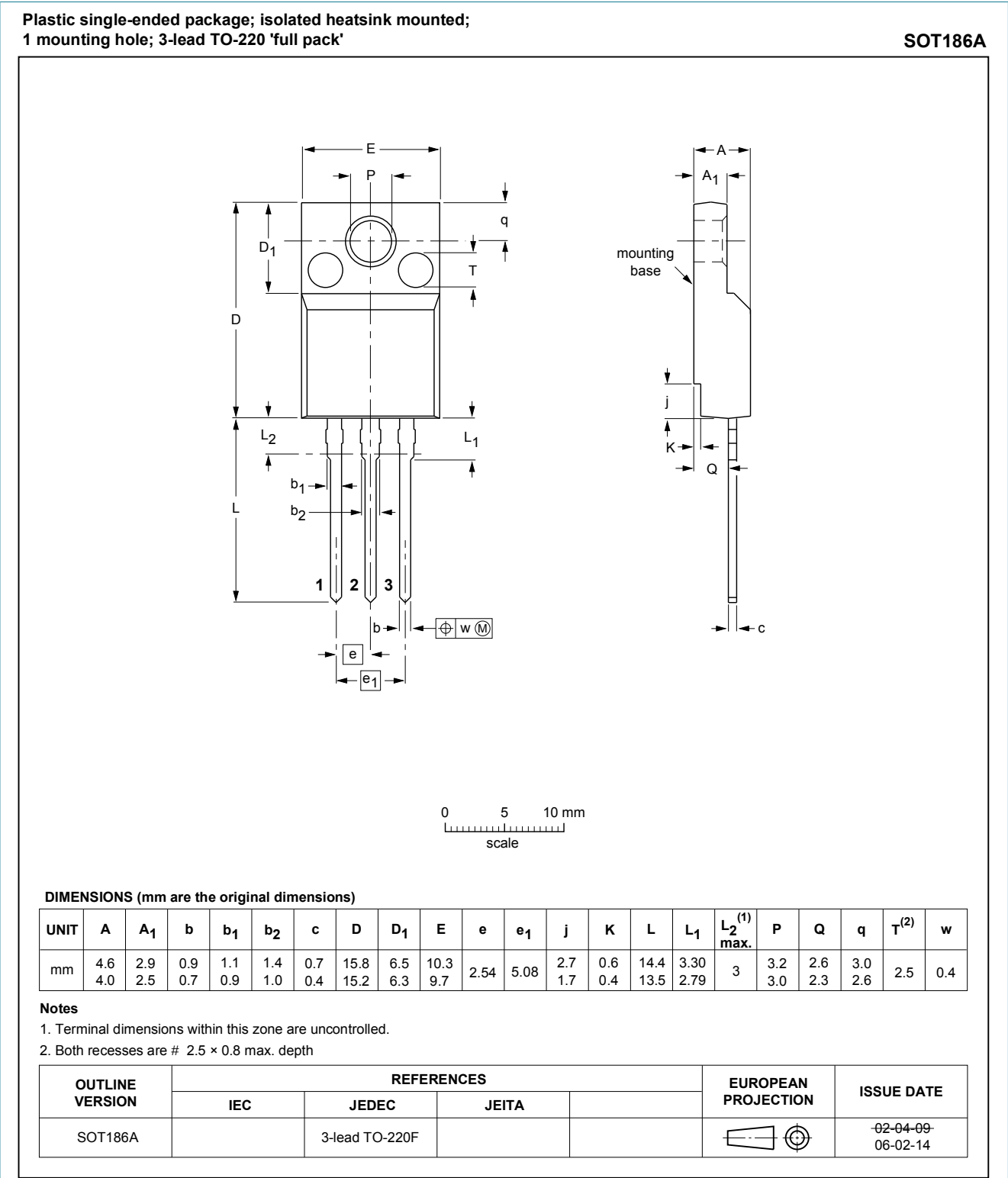


Fig. 13. Package outline TO-220F (SOT186A)

## 13. Legal information

### 13.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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